

REMARKS/ARGUMENTS

Claims 1-17 are pending. Claims 18-24 have been previously withdrawn pursuant to a Restriction Requirement. No claim has been amended, canceled, or added.

Claims 1-17 were rejected under 35 U.S.C. 102(b) as being clearly anticipated by Zommer (U.S. Patent No. 6,091,086). Applicant respectfully traverse the rejection.

Claim 1 is directed to a power device. The claim recites, "a gate electrode, a source electrode, and a drain electrode provided within an active region of a semiconductor substrate of first conductivity type; and a vertical diffusion region of second conductivity provided at a periphery the active region, the vertical diffusion region extending continuously from a top surface of the substrate to a bottom surface of the substrate, the vertical diffusion region including: an upper portion having a first depth, and a lower portion having a second depth that is substantially greater than the first depth."

The Examiner indicated that Zommer discloses "the vertical diffusion region including: an upper portion having a first depth, and a lower portion having a second depth that is substantially greater than the first depth." However, Zommer discloses that the P type region 701 (on the upper surface) and the P type region 703 (on the lower surface) **both** are provided with an impurity having a higher mobility than the P type well region [116] (emphasis added). See Col. 6, lines 43-47. It does not state that the region 703 is provided with an impurity that has a higher mobility than an impurity provided for the region 701, as the Examiner appears to be suggesting. Therefore, claim 1 is allowable. Claims 2-10 depend from claim 1 and are allowable at least for this reason.

Claim 11 recites, "a gate region, a source region, and a drain region provided in an active region of a semiconductor substrate of first conductivity type, the substrate having a front side and a backside; a scribe diffusion region of second conductivity type provided around the active region, the scribe diffusion region extending continuously from the front side of the substrate to the backside of the substrate, the scribe diffusion region comprising an impurity of first type and an impurity of second type different from the impurity of first type." Zommer does

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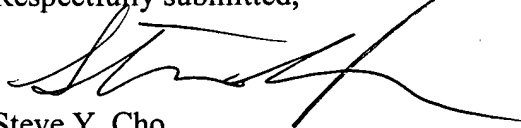
not appear to disclose the above recited features. Therefore, claim 11 is allowable. Claims 12-17 depend from claim 11 and are allowable at least for this reason.

CONCLUSION

In view of the foregoing, Applicants believe all claims now pending in this Application are in condition for allowance. The issuance of a formal Notice of Allowance at an early date is respectfully requested.

If the Examiner believes a telephone conference would expedite prosecution of this application, please telephone the undersigned at 650-326-2400.

Respectfully submitted,



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